Supplementary information

New Dithiooxamide Derivatives as Promising Precursors for ALD/MLD applications

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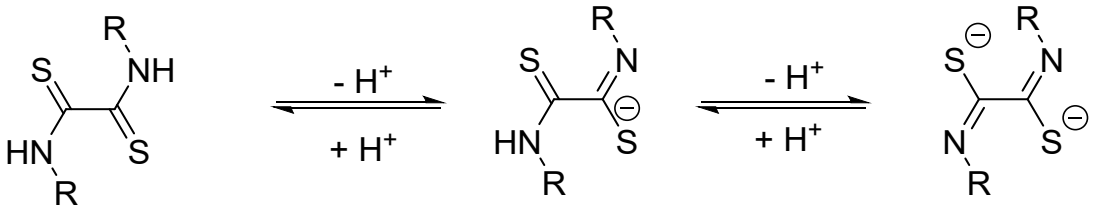
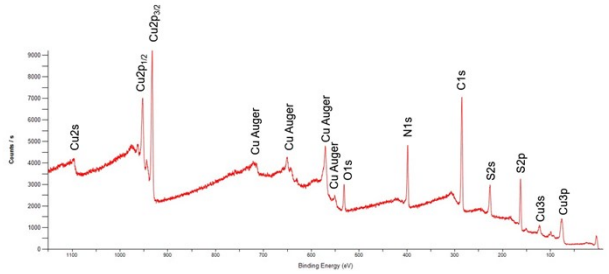
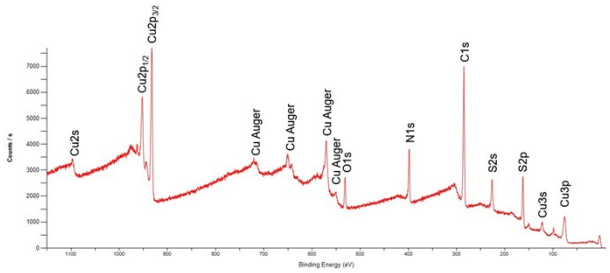


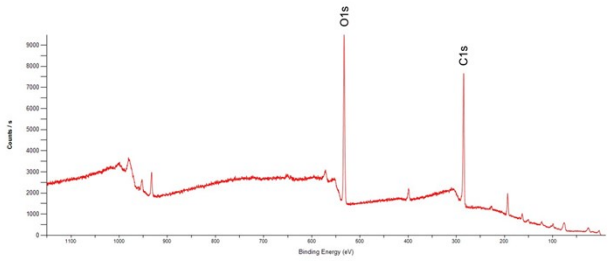
Figure S1: Redox behavior of DTOA derivatives.



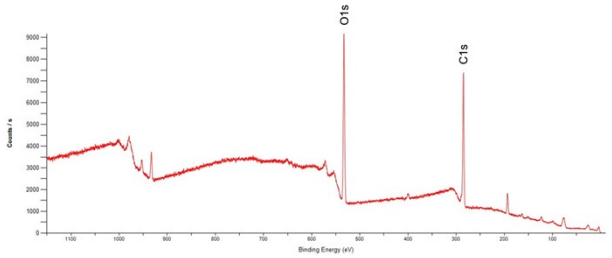
Cu-Et DTOA 2		Concentration (atomic %)	
Element	Stoichiometry	Calculated	Experimental
Cu	1	9	9.75
C	6	55	53.9
N	2	18	18
S	2	18	13.1
O	0	0	5.25



Cu-nPr DTOA 4		Concentration (atomic %)	
Element	Stoichiometry	Calculated	Experimental
Cu	1	8	8.9
C	8	62	58.4
N	2	15	14.4
S	2	15	12.9
O	0	0	5.4



Cu-iPr DTOA 3		Concentration (atomic %)	
Element	Stoichiometry	Calculated	Experimental
Cu	1	8	4
C	8	62	56.2
N	2	15	4.8
S	2	15	3.1
O	0	0	31.9



Cu-nBu DTOA 5		Concentration (atomic %)	
Element	Stoichiometry	Calculated	Experimental
Cu	1	7	4
C	10	67	57.9
N	2	13	3.1
S	2	13	2.2
O	0	0	32.8

Figure S2: XPS survey spectra of Cu-R DTOA thin films by ALD.